

Silicon NPN Power Transistors

2SC2556 2SC2556A

DESCRIPTION

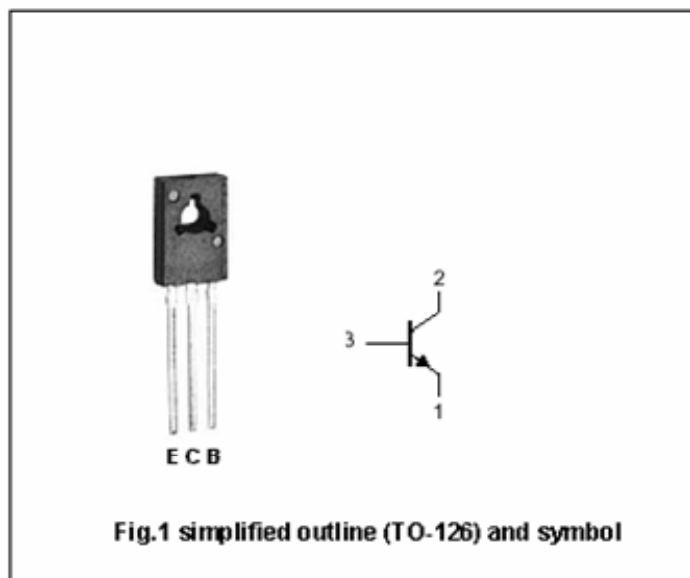
- With TO-126 package
- High V_{CBO}
- Low collector saturation voltage
- High transition frequency

APPLICATIONS

- Audio frequency output amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC2556	130	V
		2SC2556A	180	
V_{CEO}	Collector- emitter voltage	2SC2556	40	V
		2SC2556A	50	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1	A
I_{CM}	Collector current-peak		1.5	A
P_C	Collector power dissipation	$T_C=25$	1.2	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55 ~ +150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SC2556	$I_C=2mA ; I_B=0$	40			V
		2SC2556A		50			
$V_{(BR)CBO}$	Collector-base breakdown voltage	2SC2556	$I_C=10 \mu A ; I_E=0$	130			V
		2SC2556A		180			
$V_{(BR)EBO}$	Emitter-base breakdown voltage		$I_E=10 \mu A ; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage		$I_C=500mA ; I_B=50mA$			0.5	V
I_{CBO}	Collector cut-off current		$V_{CB}=120V ; I_E=0$			0.1	μA
h_{FE-1}	DC current gain		$I_C=1A ; V_{CE}=0.5V$	150		350	
h_{FE-2}	DC current gain		$I_C=0.5A ; V_{CE}=2V$	150			
C_{OB}	Output capacitance		$I_E=0 ; V_{CB}=20V ; f=1MHz$			30	pF
f_T	Transition frequency		$I_C=50mA ; V_{CE}=10V$		200		MHz

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PACKAGE OUTLINE

